Nch 500V 16A Power MOSFET

| V _{DSS} | 500V |
|----------------------------|-------|
| R _{DS(on)} (Max.) | 0.27Ω |
| I _D | ±16A |
| P _D | 77W |

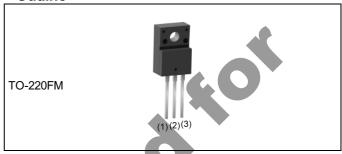
Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be ±30V.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

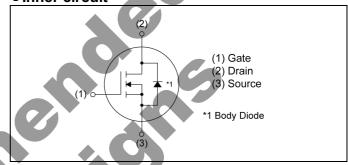
Application

Switching Power Supply

Outline



•Inner circuit



| - 1 0011013 | | |
|-------------|---------------------------|----------|
| | Packing | Bulk |
| Туре | Reel size (mm) | - |
| | Tape width (mm) | - |
| | Basic ordering unit (pcs) | 500 |
| | Taping code | - |
| | Marking | R5016ANX |

● Absolute maximum ratings (T_a = 25°C ,unless otherwise specified)

| Parameter | Symbol | Value | Unit | |
|---|------------------------|--------------------|------|------|
| Drain - Source voltage | V_{DSS} | 500 | V | |
| Continuous drain augrant | T _C = 25°C | I _D *1 | ±16 | Α |
| Continuous drain current | T _C = 100°C | I _D *1 | ±7.8 | Α |
| Pulsed drain current | I _{DP} *2 | ±64 | Α | |
| Gate - Source voltage | | V_{GSS} | ±30 | V |
| Avalanche current, single pulse | I _{AS} *3 | 8 | Α | |
| Avalanche energy, single pulse | | E _{AS} *3 | 17 | mJ |
| Avalanche energy, repetitive | | E _{AR} *4 | 3.5 | mJ |
| Power dissipation (T _c = 25°C) | P _D | 77 | W | |
| Junction temperature | T _j | 150 | °C | |
| Operating junction and storage temper | T _{stg} | -55 to +150 | °C | |
| Reverse diode dv/dt | | dv/dt | 15 | V/ns |

Absolute maximum ratings

| Parameter | Symbol | Conditions | Values | Unit |
|------------------------------|--------|--|--------|------|
| Drain - Source voltage slope | dv/dt | $V_{DS} = 400V, I_{D} = 16A$ $T_{j} = 125^{\circ}C$ | 50 | V/ns |

●Thermal resistance

| Doramatar | Symbol | Values | | | Unit | |
|---|-------------------|--------|--------|------|------|--|
| Parameter | Symbol | Min. | Тур. | Max. | Unit | |
| Thermal resistance, junction - case | R _{thJC} | - | - | 1.62 | °C/W | |
| Thermal resistance, junction - ambient | R _{thJA} | | - | 70 | °C/W | |
| Soldering temperature, wavesoldering for 10s | T _{sold} | | - | 265 | °C | |
| ●Electrical characteristics (T _a = 25°C) | | | | | | |
| | | | Values | | | |

● Electrical characteristics (T_a = 25°C)

| Parameter | Symbol Conditions | | | Values | | Unit |
|---|------------------------|--|------|--------|------|-------|
| r alametei | Symbol | Conditions | Min. | Тур. | Max. | Offic |
| Drain - Source breakdown voltage | V _{(BR)DS\$} | $V_{GS} = 0V, I_D = 1mA$ | 500 | - | ı | V |
| Drain - Source avalanche breakdown voltage | V _{(BR)DS} | $V_{GS} = 0V, I_D = 8A$ | ı | 580 | ı | V |
| | | $V_{DS} = 500V, V_{GS} = 0V$ | | | | |
| Zero gate voltage drain current | I _{DSS} | $T_j = 25^{\circ}C$ | - | 0.1 | 100 | μA |
| | | T _j = 125°C | - | - | 1000 | |
| Gate - Source leakage current | I _{GSS} | V _{GS} = ±30V, V _{DS} = 0V | - | - | ±100 | nA |
| Gate threshold voltage | V _{GS(th)} | V _{DS} = 10V, I _D = 1mA | 2.5 | - | 4.5 | V |
| | | V _{GS} = 10V, I _D = 8A | | | | |
| Static drain - source on - state resistance | R _{DS(on)} *6 | T _j = 25°C | - | 0.21 | 0.27 | Ω |
| on state regionality | | T _j = 125°C | - | 0.45 | - | |
| Gate resistance | R_{G} | f = 1MHz, open drain | - | 10 | - | Ω |

● Electrical characteristics (T_a = 25°C)

| Parameter | Cumbal | Conditions | Values | | | Unit |
|--|------------------------|---|--------|------|------|--------|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Offic |
| Forward Transfer Admittance | Y _{fs} *6 | V _{DS} = 10V, I _D = 8A | 6 | 12 | _ | S |
| Input capacitance | C _{iss} | V _{GS} = 0V | - | 1800 | | |
| Output capacitance | C _{oss} | V _{DS} = 25V | - | 750 | 5) | pF |
| Reverse transfer capacitance | C _{rss} | f = 1MHz | - | 55 | _ | |
| Effective output capacitance, energy related | C _{o(er)} | V _{GS} = 0V, | | 68.2 | - | ا ا |
| Effective output capacitance, time related | C _{o(tr)} | V _{DS} = 0V to 400V | | 222 | - | pF |
| Turn - on delay time | t _{d(on)} *6 | V _{DD} ≈ 250V, V _{GS} = 10V | - | 40 | - | |
| Rise time | t _r *6 | I _D = 8A | (| 50 | - | 200 |
| Turn - off delay time | t _{d(off)} *6 | R _L ≃ 31.3Ω | | 150 | 300 | ns |
| Fall time | t _f *6 | $R_G = 10\Omega$ | | 55 | 110 | |

● Gate charge characteristics (T_a = 25°C)

| Parameter | Symbol | Symbol Conditions - | | Values | | |
|----------------------|------------------------|------------------------------------|------|--------|------|------|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit |
| Total gate charge | Q _g *6 | V _{DD} ≈ 250V | - | 50 | 1 | |
| Gate - Source charge | Q _{gs} *6 | I _D = 16A | - | 9.5 | 1 | nC |
| Gate - Drain charge | Q _{gd} *6 | V _{GS} = 10V | - | 21 | 1 | |
| Gate plateau voltage | V _(plateau) | $V_{DD} \simeq 250V$, $I_D = 16A$ | - | 5.8 | ı | V |

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw ≤ 10µs, Duty cycle ≤ 1%

^{*3} L $^{\sim}500\mu\text{H},\,\text{V}_{DD}$ =50V, R $_{G}$ =25 Ω , starting T $_{j}$ =25 $^{\circ}\text{C}$

^{*4} L $^\sim$ 500 μ H, V_{DD}=50V, R_G=25 Ω , starting T_j=25 $^\circ$ C, f=10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

| Darameter | Cymbol | Conditions | Values | | | Unit |
|---|----------------------|---|--------|------|------|-------|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Offic |
| Continuous forward current | I _S *1 | T - 25°C | 1 | ı | 16 | А |
| Pulse forward current | I _{SP} *2 | T _C = 25°C | - | - | 64 | А |
| Forward voltage | V _{SD} *6 | $V_{GS} = 0V, I_{S} = 16A$ | - | - | 1.5 | V |
| Reverse recovery time | t _{rr} *6 | | - | 422 | - | ns |
| Reverse recovery charge | Q _{rr} *6 | I _S = 16A di/dt = 100A/µs | | 4.82 | - | μC |
| Peak reverse recovery current | I _{rrm} *6 | αναι 100/ γμο | | 22.8 | - | Α |
| Peak rate of fall of reverse recovery current | di _{rr} /dt | T _j = 25°C | - | 700 | - | A/µs |

• Typical transient thermal characteristics

| Symbol | Value | Unit |
|------------------|-------|------|
| R _{th1} | 0.117 | |
| R _{th2} | 0.662 | k/W |
| R _{th3} | 2.15 | |

| Symbol | Value | Unit |
|------------------|---------|------|
| C _{th1} | 0.00318 | |
| C _{th2} | 0.0429 | Ws/K |
| C _{th3} | 0.507 | |

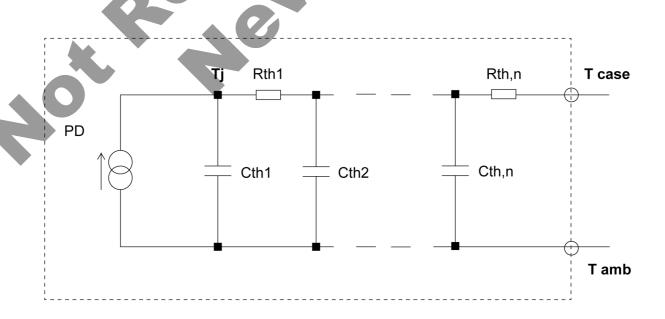


Fig.1 Power Dissipation Derating Curve

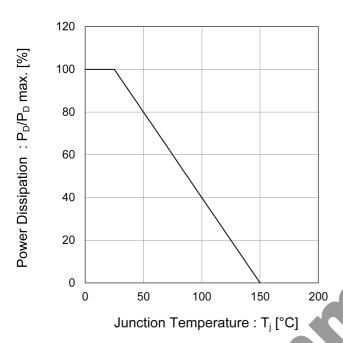
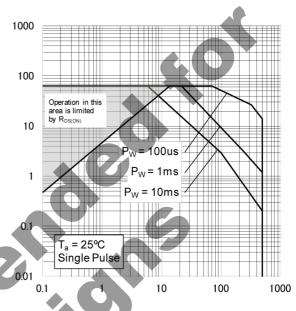


Fig.2 Maximum Safe Operating Area



Drain Current : I_D [A]

Drain - Source Voltage : V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

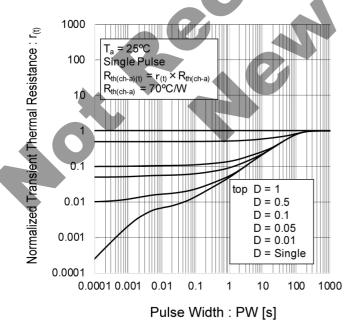


Fig.4 Avalanche Current vs. Inductive Load

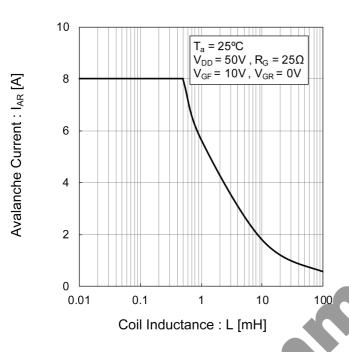


Fig.5 Avalanche Power Losses

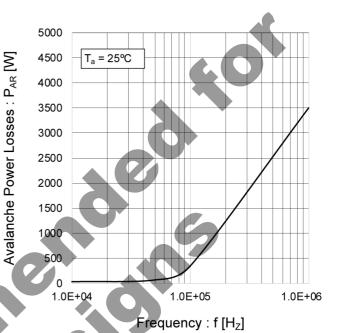


Fig.6 Avalanche Energy Derating Curve vs. Junction Temperature

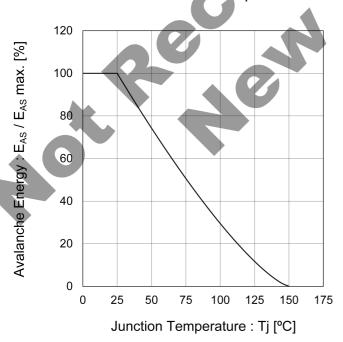
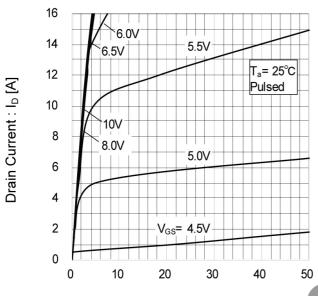
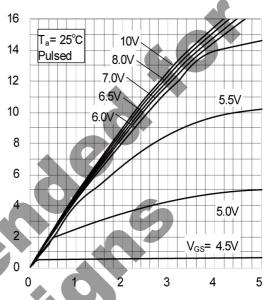


Fig.7 Typical Output Characteristics(I)



Drain - Source Voltage : $V_{DS}[V]$

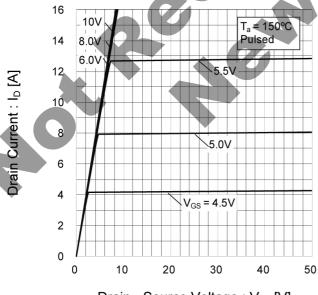
Fig.8 Typical Output Characteristics(II)



Drain Current : I_D [A]

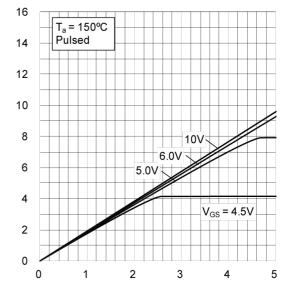
Drain - Source Voltage : V_{DS} [V]

Fig.9 Tj = 150°C Typical Output Characteristics (I)



Drain - Source Voltage : $V_{DS}[V]$

Fig.10 Tj = 150°C Typical Output Characteristics (II)



Drain - Source Voltage : V_{DS} [V]

Drain Current : I_D [A]

Fig.11 Breakdown Voltage vs. Junction Temperature

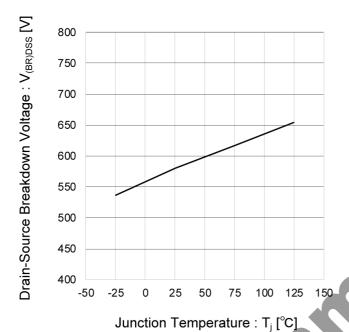


Fig.12 Typical Transfer Characteristics

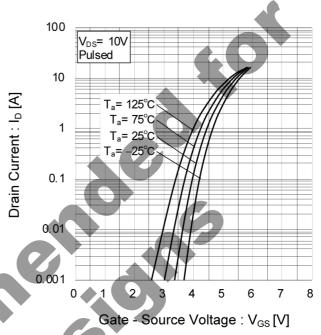


Fig.13 Gate Threshold Voltage Junction Temperature

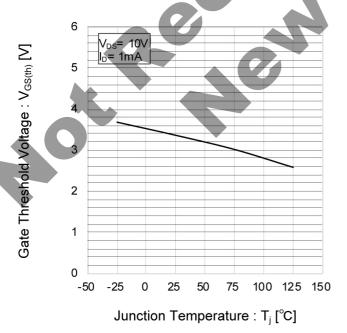
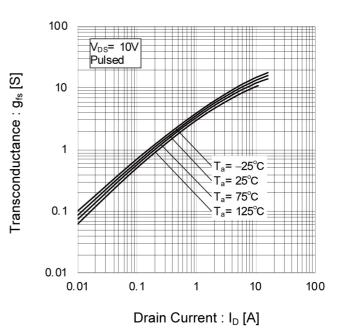


Fig.14 Transconductance vs. Drain Current

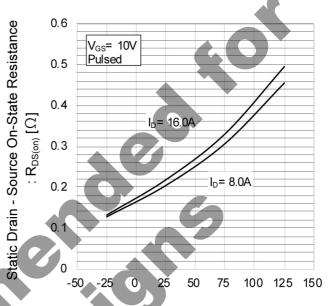


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Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

Static Drain - Source On-State Resistance 0.6 T_a=25°C 0.5 Pulsed 0.4 $R_{DS(on)}[\Omega]$ $I_D = 16.0A$ $I_D = 8.0A$ 0.3 0.2 0.1 0 5 10 Gate - Source Voltage : V_{GS} [V]

Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature



Junction Temperature : T_j [°C]

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

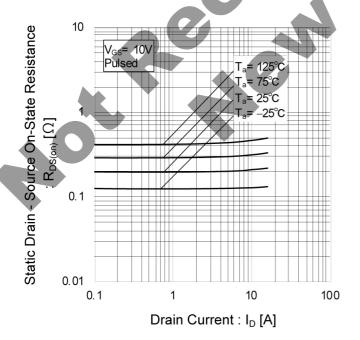


Fig.18 Typical Capacitance vs. Drain - Source Voltage

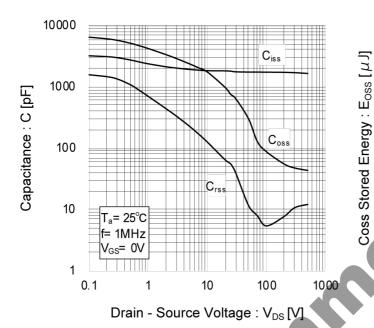


Fig.19 Coss Stored Energy

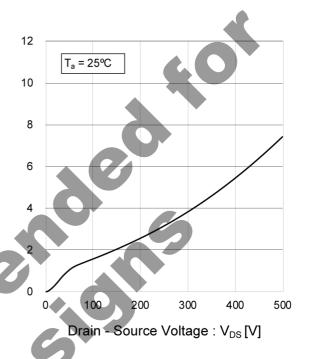


Fig.20 Switching Characteristics

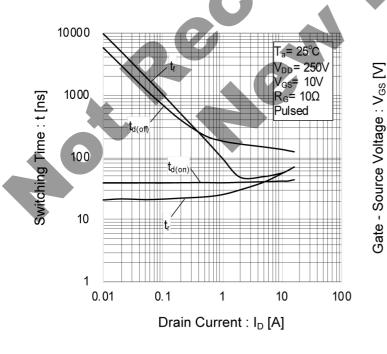


Fig.21 Dynamic Input Characteristics

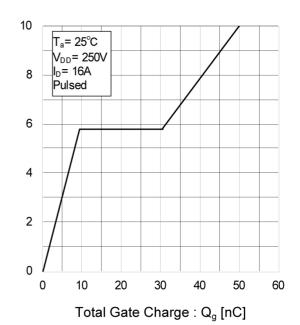


Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

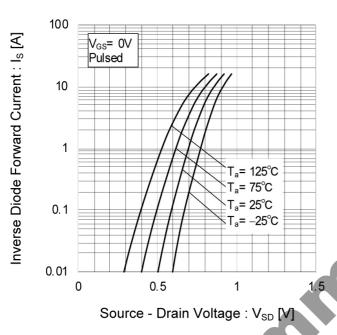
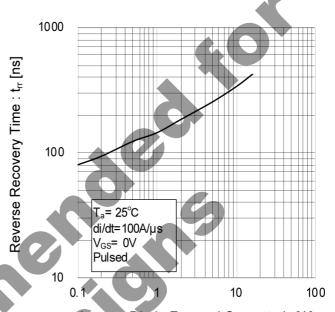


Fig.23 Reverse Recovery Time vs.
Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

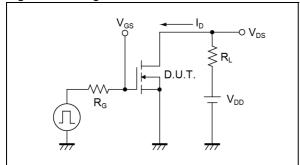


Fig.2-1 Gate Charge Measurement Circuit

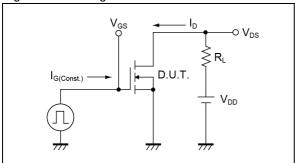


Fig.3-1 Avalanche Measurement Circuit

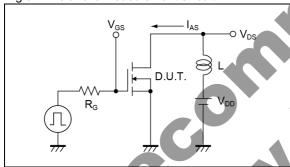


Fig.4-1 dv/dt Measurement Circuit

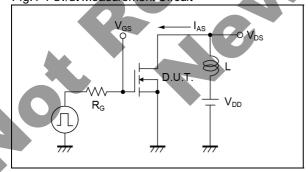


Fig.5-1 di/dt Measurement Circuit

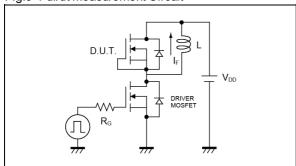


Fig.1-2 Switching Waveforms

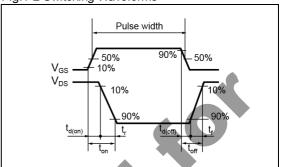


Fig.2-2 Gate Charge Waveform

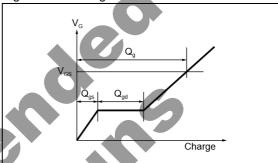


Fig.3-2 Avalanche Waveform

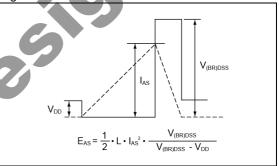


Fig.4-2 dv/dt Waveform

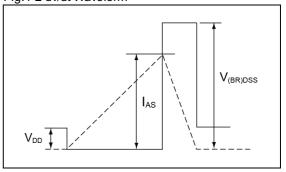
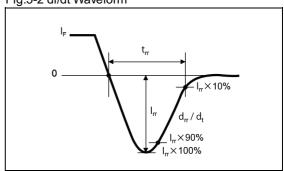
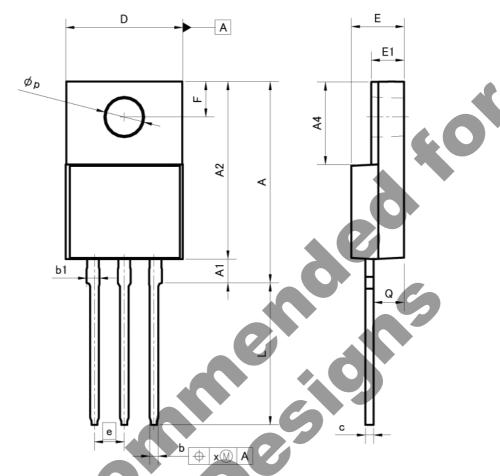


Fig.5-2 di/dt Waveform



Dimensions





| DIM | MILIMETERS | | INC | HES |
|-----|------------|-------|-------|-------|
| DIM | MIN | MAX | MIN | MAX |
| A | 16.60 | 17.60 | 0.654 | 0.693 |
| A1 | 1.80 | 2.20 | 0.071 | 0.087 |
| A2 | 14.80 | 15.40 | 0.583 | 0.606 |
| A4 | 6.80 | 7.20 | 0.268 | 0.283 |
| b | 0.70 | 0.90 | 0.028 | 0.035 |
| b1 | 1.10 | 1.50 | 0.043 | 0.059 |
| С | 0.70 | 0.85 | 0.028 | 0.033 |
| D | 9.90 | 10.30 | 0.390 | 0.406 |
| E | 4.40 | 4.80 | 0.173 | 0.189 |
| е | 2. | 54 | 0.1 | 00 |
| E1 | 2.70 | 3.00 | 0.106 | 0.118 |
| F | 2.80 | 3.20 | 0.110 | 0.126 |
| L | 11.50 | 12.50 | 0.453 | 0.492 |
| р | 3.00 | 3.40 | 0.118 | 0.134 |
| Q | 2.10 | 3.10 | 0.083 | 0.122 |
| х | - | 0.38 | _ | 0.015 |

Dimension in mm/inches



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| JAPAN | USA | EU | CHINA |
|---------|---------|------------|---------|
| CLASSⅢ | CLASSII | CLASS II b | CLASSII |
| CLASSIV | | CLASSⅢ | |

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 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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Notice-PGA-E Rev.003